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PATENT

#3/election
6-26-02
JD

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of)

Inventor: Vladislav Vashchenko et. al.)

Serial No.: 09/896,681)

Filed: June 29, 2001)

Title: HIGH HOLDING VOLTAGE)

LVTSCR)

Art Unit: 2815

Examiner: Joseph H. Nguyen

Commissioner for Patents
Washington, D.C. 20231

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RESPONSE TO RESTRICTION/ELECTION REQUIREMENT

The examiner is thanked for his Office action mailed 5/17/2002, which has been studied in detail.

Applicant elects Group I, Claims 1-7, 11-16, drawn to an ESD protection structure.

The restriction/election requirement further requires election of a species comprising an embodiment illustrated in Figure 3, 4, 5, 6, or 7.

For completeness, the claims relating to Figure 3 are elected. Claims 1-4 and 11 relate to Figure 3.

However, it is respectfully submitted that the claims 1-4 and 11 apply to all of the above embodiments and thus constitute generic claims. The reference to p+ emitter and the n+ drain

region both include either a single or a plurality of regions, i.e., the singular includes the plural, according to common claiming convention. This is also emphasized by the fact that the dependent claims (e.g., claims 5 and 7), specifically include the possibility that the p+ emitter and n+ drain region could be made up of more than one region.

It is therefore, respectfully submitted that contrary to the statement made in the Office action, there are generic claims. It is, therefore, respectfully requested that all of the generic claims be examined and, if found allowable, that all of the disclosed species be prosecuted on their merit.

While an election has been made of Group I, drawn to the structure, for completeness, it is pointed out that the terminology in the application relating to "splitting the n+ drain region" does not intend to suggest that there is a physical forming of a single region that is subsequently split. This would not be possible in a process environment in which regions are formed by performing selective masking and doping steps. The term "splitting" was used merely for convenience to indicate that the drain is formed in more than one part.

Respectfully Submitted,

Dated: 6/3/, 2002



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